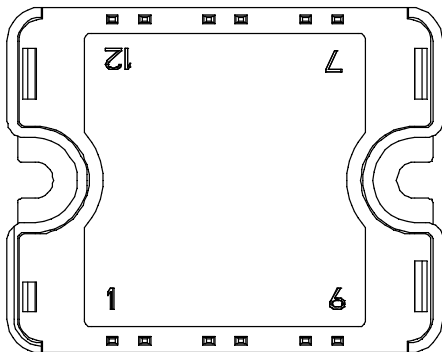
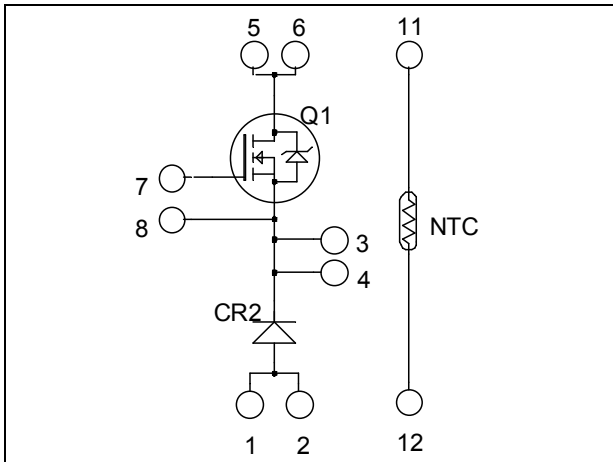


## Buck chopper Super Junction MOSFET Power Module

$V_{DSS} = 800V$   
 $R_{DSon} = 150m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 28A \text{ @ } T_c = 25^\circ C$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- **COOLMOS**  
Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	800	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	28
		$T_c = 80^\circ C$	21
$I_{DM}$	Pulsed Drain current	110	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	150	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	277
$I_{AR}$	Avalanche current (repetitive and non repetitive)	17	A
$E_{AR}$	Repetitive Avalanche Energy	0.5	mJ
$E_{AS}$	Single Pulse Avalanche Energy	670	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 800V$			50	$\mu\text{A}$
		$T_j = 25^\circ\text{C}$				
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 0V, V_{DS} = 800V$			150	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$				
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2\text{mA}$	2.1	3	3.9	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 150$	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		4507		pF
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		2092		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		108		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 28A$		180		nC
$Q_{gs}$	Gate – Source Charge			22		
$Q_{gd}$	Gate – Drain Charge			90		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @125°C</b> $V_{GS} = 15V$ $V_{Bus} = 533V$ $I_D = 28A$ $R_G = 2.5\Omega$		10		ns
$T_r$	Rise Time			13		
$T_{d(off)}$	Turn-off Delay Time			83		
$T_f$	Fall Time			35		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ 25°C</b> $V_{GS} = 15V, V_{Bus} = 533V$ $I_D = 28A, R_G = 2.5\Omega$		486		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			278		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ 125°C</b> $V_{GS} = 15V, V_{Bus} = 533V$ $I_D = 28A, R_G = 2.5\Omega$		850		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			342		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$I_F$	DC Forward Current	$T_c = 80^\circ\text{C}$		30		A
$V_F$	Diode Forward Voltage	$I_F = 30A$		2.6	3.1	V
		$I_F = 60A$		3.2		
		$I_F = 30A$	$T_j = 125^\circ\text{C}$	1.8		
$t_{rr}$	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	300		ns
			$T_j = 125^\circ\text{C}$	380		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	360		nC
			$T_j = 125^\circ\text{C}$	1700		

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	Transistor		0.45	°C/W	
		Diode		1.2		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

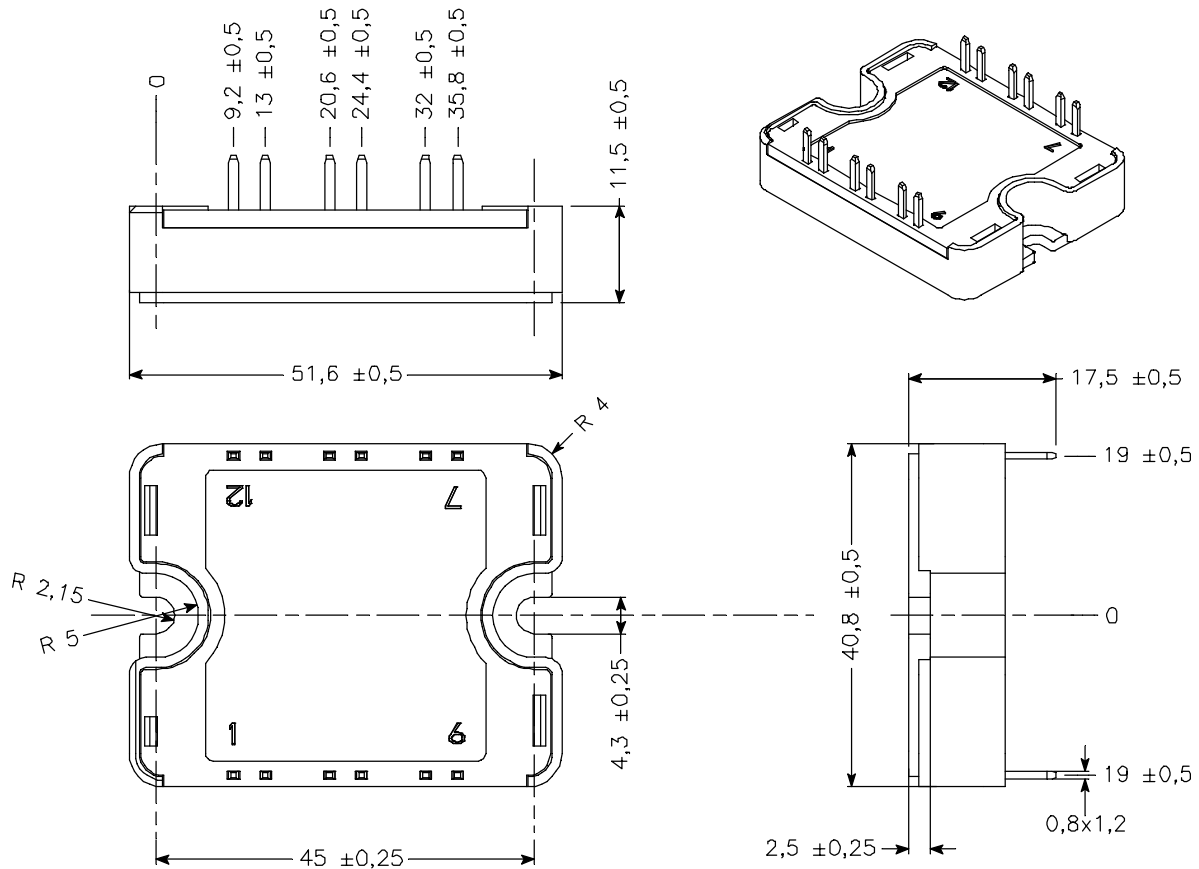
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

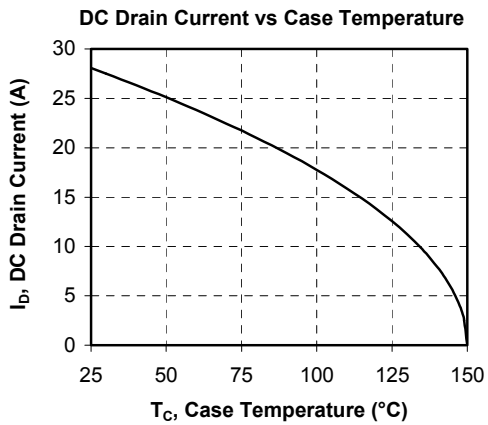
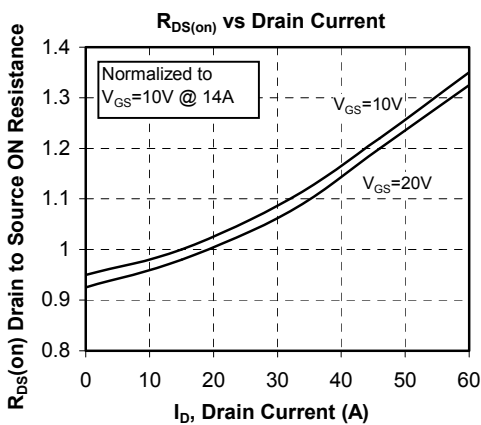
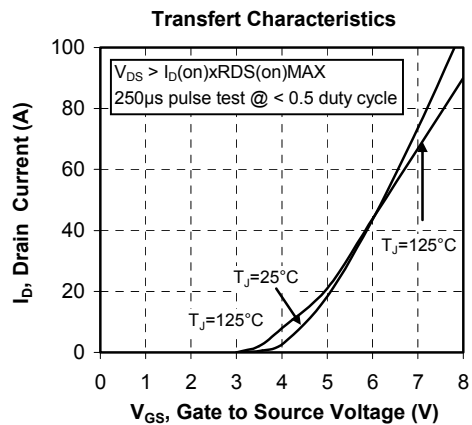
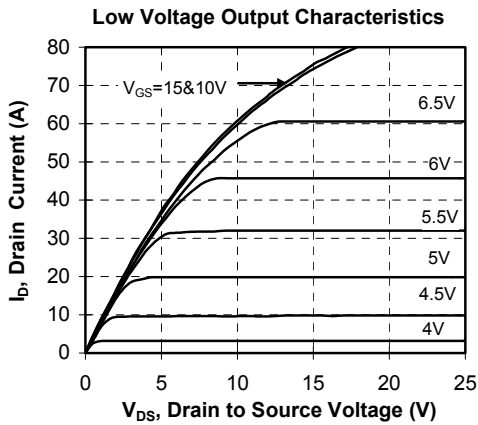
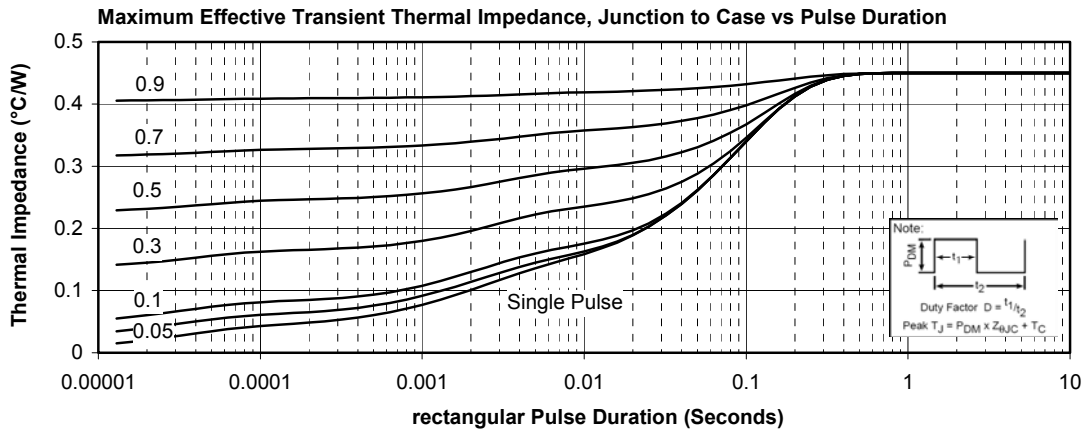
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

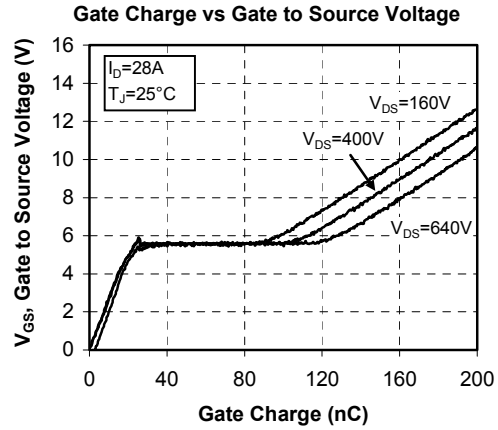
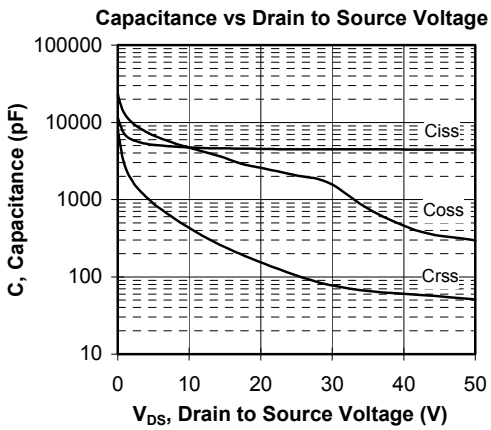
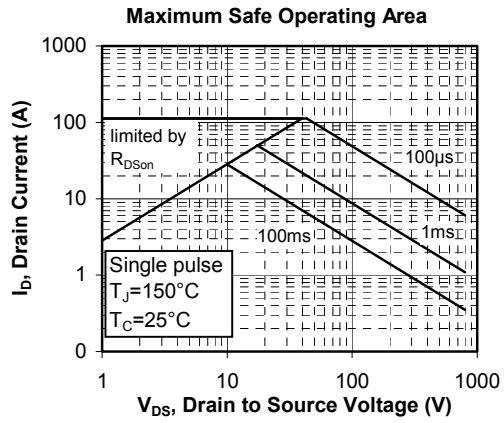
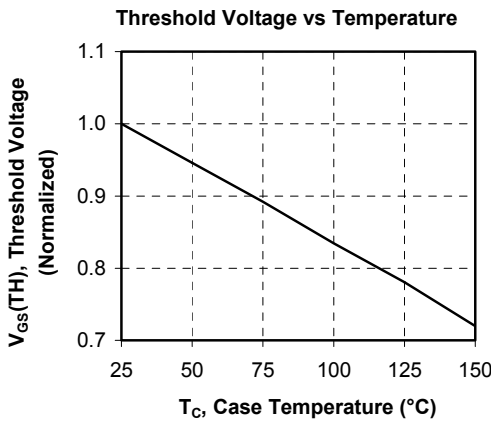
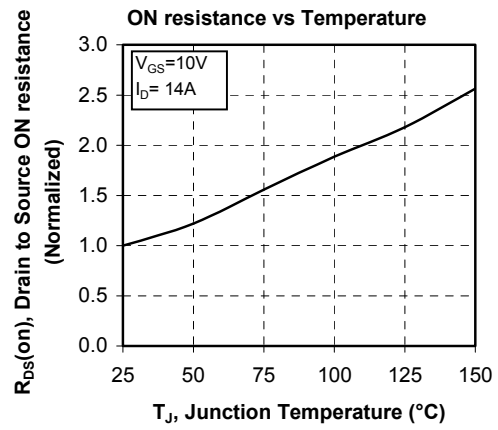
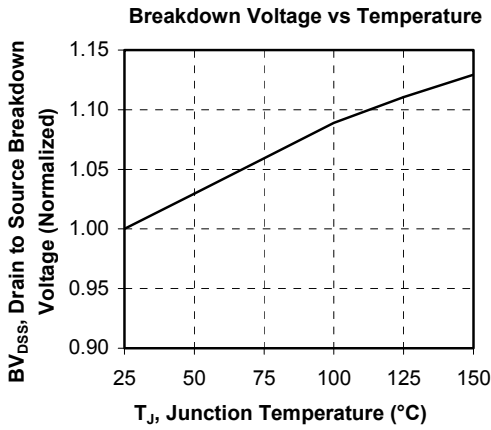
## SP1 Package outline (dimensions in mm)

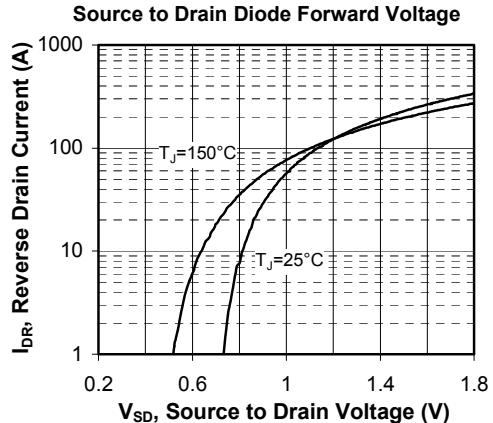
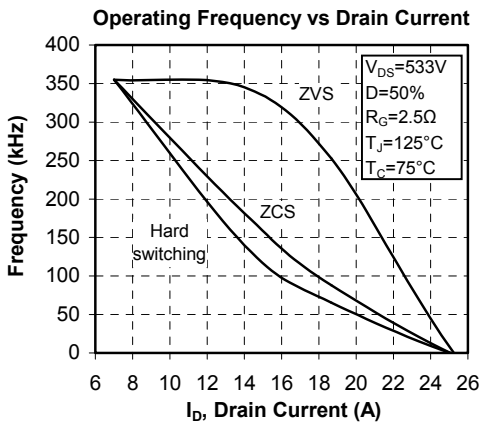
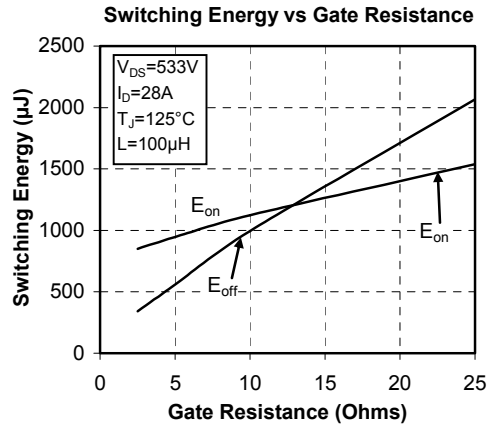
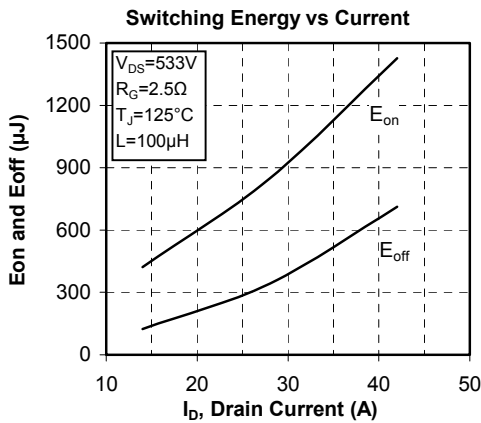
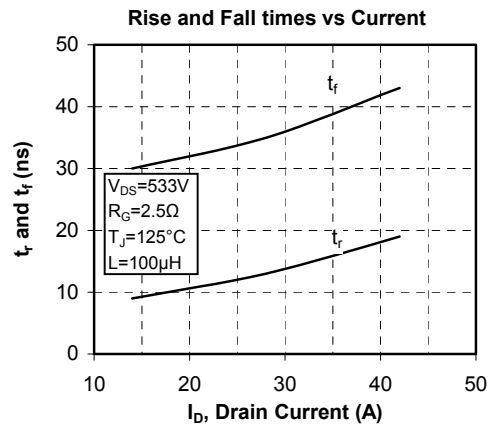
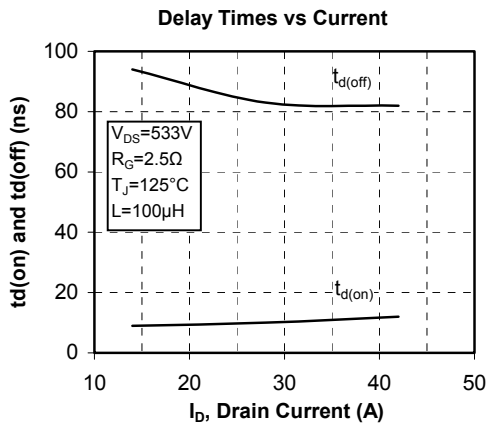


See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve







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